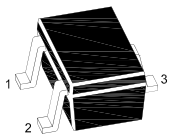
MMBTA14W

NPN Silicon Epitaxial Planar Transistors

for general purpose applications, darlington transistor.



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Emitter Voltage	V_{CES}	30	V
Collector Base Voltage	V_{CBO}	30	V
Emitter Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{Stg}	-55 to +150	℃

Characteristics at T_{amb} = 25℃

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at V_{CE} = 5 V, I_C = 10 mA at V_{CE} = 5 V, I_C = 100 mA	 h_{FE} h_{FE}	 10000 20000	 - -	 - -
Collector Emitter Breakdown Voltage at I_C = 100 µA	$V_{(BR)CES}$	30	-	V
Collector Cutoff Current at V_{CB} = 30 V	I_{CBO}	-	100	nA
Emitter Cutoff Current at V_{EB} = 10 V	I_{EBO}	-	100	nA
Collector Emitter Saturation Voltage at I_C = 100 mA, I_B = 0.1 mA	$V_{CE\ (sat)}$	-	1.5	V
Base Emitter On Voltage at I_C = 100 mA, V_{CE} = 5 V	$V_{BE(on)}$	-	2	V
Current Gain Bandwidth Product at V_{CE} = 5 V, I_C = 10 mA, f = 100 MHz	f_T	125	-	MHz